

Process		38 um Thick Photoresist Process	
		AZ 9260	
Dehydration Bake (hot plate)	temp (°C)	200	
	time (min)	5	
HMDS (dynamic) spin	speed (rpm)	2000	
	time (s)	30	
Spin coating AZ9260	speed (rpm)	300	
	time (s)	3	
	speed (rpm)	900	
	acceleration (rpm/s)	1500	
	time (s)	80	
Wait	time (s)	60	
Soft-bake (hotplate)	temp (°C)	90	
	time (min)	1	
	temp (°C)	110	
	time (min)	4	
If double coating, repeat spin coating step above			
Wait	time (s)	60	
Soft-bake (hotplate)	temp (°C)	90	
	time (min)	1	
	temp (°C)	110	
	time (min)	8	
Wait	time (s)	60	
Expose (12mW/cm <sup>2</sup> )	mode	SC (multiple exposure 3 cycles 30 sec each w/ 10 sec gap)	
	time (s)	90	
Develop	developer	AZ 400K	
	developer: di water ratio	1:4	

1. Use a minimum of 100 ml of AZ 400K developer for a 4-inch wafer to avoid the slow-down of the development rate due to insufficient developer quantity. On bigger features it is possible to see the progress of development. Allow a little over-development, once resist has cleared.
2. These results are based on using a bare Silicon substrate. Films present on substrates and/or other types of substrates may affect the exposure and/or development time. Adjust as needed.